

Sub C1

BK

In the Claims:

1. (Twice Amended) A semiconductor device, comprising:

a trench formed in a substrate;

a diffusion region surrounding the trench to form a buried plate;

a first conductive material formed in the trench, wherein the first conductive material makes contact to the buried plate to form a first electrode, said contact being made along an entire bottom portion of the trench and along a lower portion of the sidewalls of the trench;

a second conductive material disposed in the trench to form a second electrode; and

a node dielectric layer formed between the first electrode and the second electrode.

REMARKS

Claims 1-6 are pending in the application and stand rejected. Claim 1 has been amended. A marked up version of the claim amendment is annexed hereto. Applicant respectfully requests reconsideration of the claim rejections based on the above amendment and the following remarks.

Claims 1-4 and 6 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Park (U.S. Patent No. 5,677,225) in view of Wu (U.S. Patent No. 5,985,729). Claim 5 stands rejected under 35 U.S.C. § 103(a) as being unpatentable over Park and Wu as applied to claim 1 above, and further in view of Chang (US 6,077,739).

At the very minimum, claim 1 is believed to be non-obvious over the combination of Park and Wu because the combination does not disclose or suggest, *inter alia*, a first conductive material formed in the trench, wherein the first conductive material makes contact to the buried